



INFORMATION DISCLOSURE CITATION PTO-1449	Atty. Docket No. 011083	Serial No. 09/941,982
	Applicant(s): KANO, Takashi, et al.	
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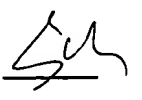
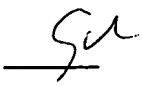
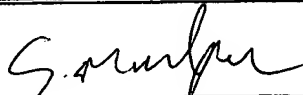
U.S. PATENT DOCUMENTS

Examiner Initial	Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
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FOREIGN PATENT DOCUMENTS

Document No.	Date	Country	Translation (Yes or No)
_____	AE		
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OTHER DOCUMENTS

 	AK	Stacia KELLER, Effect of the Trimethylgallium Flow during Nucleation Layer Growth on the Properties of GaN Grown on Sapphire, Jpn. J. Appl. Phys., March 1, 1996, Vol. 35, No. 3A, pp. L285-L288.
	AL	Ki Soo KIM, Effects of Growth Rate of a GaN Buffer Layer on the Properties of GaN on a Sapphire Substrate, J. Appl. Phys., June 15, 1999, Vol. 85, No. 12, pp. 8441-8444.
Examiner 		Date Considered 7/22/02